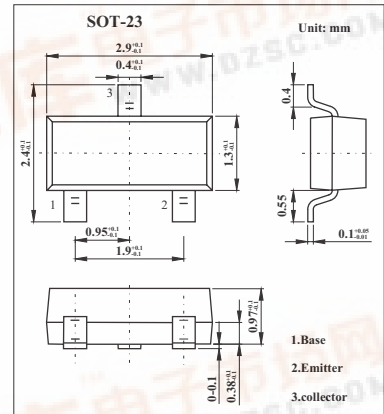


SMD Type Transistors

Medium Power Transistor  
FMMT591

■ Features

- Low equivalent on-resistance.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-80	V
Collector-emitter voltage	V <sub>CE0</sub>	-60	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Peak collector current	I <sub>CM</sub>	-2	A
Collector current	I <sub>C</sub>	-1	A
Base current	I <sub>B</sub>	-200	mA
Power dissipation	P <sub>tot</sub>	500	mW
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA	-80			V
Collector-emitter breakdown voltage *	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA	-60			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA	-5			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V			-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V			-100	nA
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA			-0.6	V
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA			-1.2	V
Base-emitter voltage *	V <sub>BE(ON)</sub>	I <sub>C</sub> =-1A, V <sub>CE</sub> =-5V			-1.0	V
Static Forward Current TransferRatio	h <sub>FE</sub>	I <sub>C</sub> =-1mA, V <sub>CE</sub> =-2V*	100			
		I <sub>C</sub> =-500mA, V <sub>CE</sub> =-5V	100		300	
		I <sub>C</sub> =-1A, V <sub>CE</sub> =-2V*	80			
		I <sub>C</sub> =-2A, V <sub>CE</sub> =-2V*	40			
Current-gain-bandwidth product	f <sub>T</sub>	I <sub>C</sub> =-50mA, V <sub>CE</sub> =-10V, f=100MHz	150			MHz
Output capacitance	C <sub>obo</sub>	V <sub>CB</sub> =-10V, f=1MHz			10	pF

\* Pulse test: t<sub>p</sub> ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	591
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